AlGaAs/GaAs T-1 3/4 PACKAGE INFRARED EMITTING DIODE

MIE-824A4

Description

The MIE-824A4 is an infrared emitting diode utilizing GaAs with AlGaAs window coation chip technology.

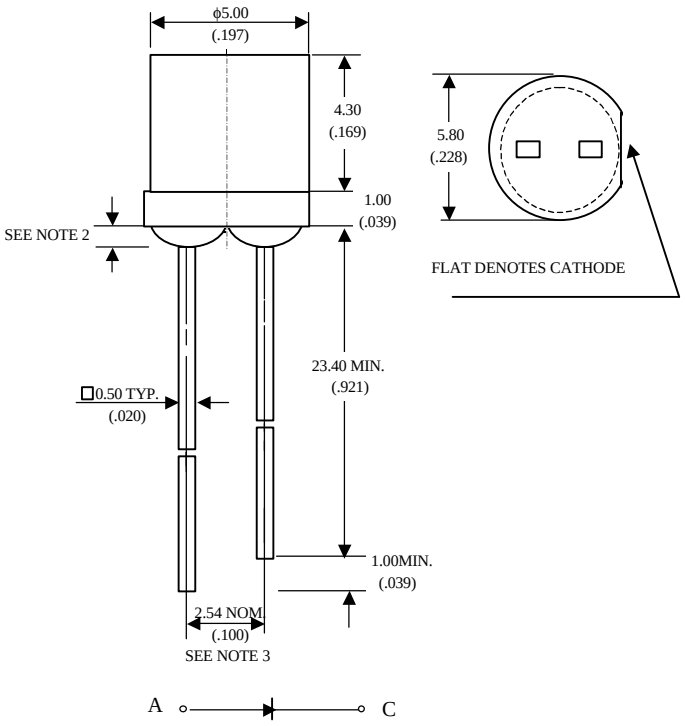
It is molded in water clear plastic package.

Features

- High radiant power and high radiant intesity
- Peak wavelength λ_p = 940 nm
- Good spectral matching to si-photodetector
- Radiant angle: 120°

Package Dimensions

Unit: inches



Notes :
1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Protruded resin under flange is 1.5 mm (.059") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ T_A=25°C

Parameter	Maximum Rating	Unit
Power Dissipation	120	mW
Peak Forward Current	1	A
Continuous Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Intensity	I_F=20mA	Ie		0.8		mW/sr
Forward Voltage	I_F=50mA	V_F		1.30	1.50	V
Reverse Current	V_R=5V	I_R			100	μA
Peak Wavelength	I_F=20mA	λ		940		nm
Spectral Bandwidth	I_F=20mA	Δλ		50		nm
View Angle	I_F=20mA	$2\theta_{1/2}$		120		deg .

Typical Optical-Electrical Characteristic Curves

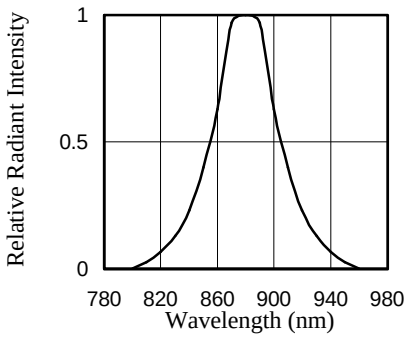


FIG.1 SPECTRAL DISTRIBUTION

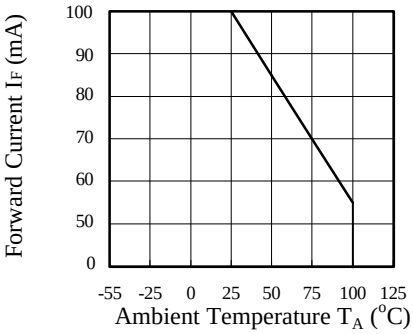


FIG.2 FORWARD CURRENT VS. AMBIENT TEMPERATURE

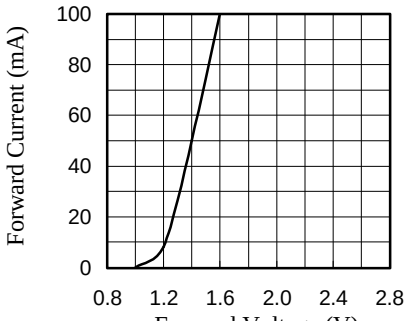


FIG.3 FORWARD CURRENT VS. FORWARD VOLTAGE

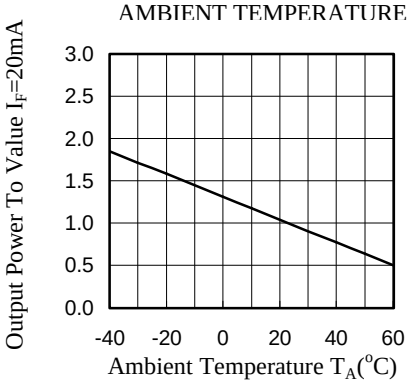


FIG.4 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

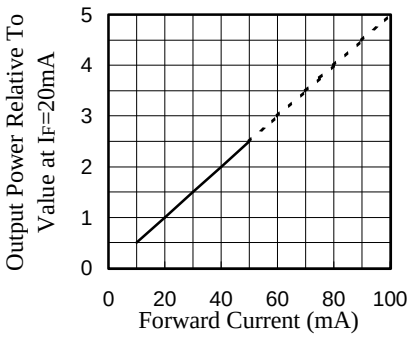


FIG.5 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

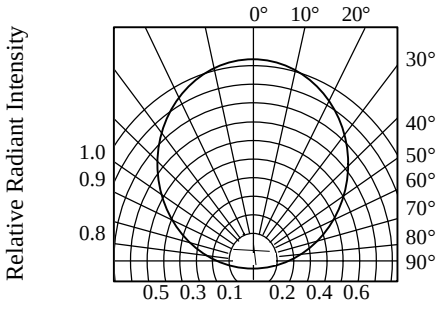


FIG.6 RADIANTION DIAGRAM